$$\Gamma(r) = \sum \Gamma(K_n) e^{iK_n \cdot r}$$

倒格矢:
$$b_1=rac{2\pi[a_2 imes a_3]}{\Omega}$$
 $b_2=rac{2\pi[a_1 imes a_3]}{\Omega}$ $b_3=rac{2\pi[a_1 imes a_2]}{\Omega}$

单电子近似电子的势函数是只关于r的函数

德布罗意: $P = \frac{h}{\lambda}$

量子牛顿方程: $f = \hbar \frac{dk}{dt} = \frac{dp}{dt}$

有效质量:
$$\frac{1}{\hbar^2}\left(\frac{\mathbf{d}^2E}{\mathbf{d}k^2}\right)_{k=0}=\frac{1}{m_{\mathrm{n}}^*}$$

电子速度: $v = \frac{\hbar k}{m_n *}$

E 到 $E+\mathrm{d}E$ 之间被电子占据的量子态 $f(E)\mathrm{g}(E)\mathrm{d}E$

导带有效能态密度:
$$N_c=2(rac{m_n^*k_0T}{2\pi\hbar^2})^{rac{3}{2}}$$
 $N_{
u}=2(rac{m_p^*k_0T}{2\pi\hbar^2})^{rac{3}{2}}$

$$p = N_
u exp(rac{E_
u - E_F}{k_
u T})$$
 $n = N_c exp(-rac{E_
u - E_F}{k_
u T})$

质量作用定律:
$$np=N_cN_
u\exp(-rac{E_c-E_
u}{k_0T})=N_cN_
u\exp(-rac{E_g}{k_0T})=n_i^2$$

本征半导体:
$$E_i=E_F=rac{E_c+E_
u}{2}+rac{k_0T}{2}\lnrac{N_
u}{N_c}=rac{E_c+E_
u}{2}+rac{3k_0T}{4}\lnrac{m_p^*}{m_s^*}$$

可借助质量作用定律推得:

$$n=n_i \exp(rac{E_F-E_i}{k_0T})$$
 $p=n_i \exp(rac{E_i-E_F}{k_0T})$

电中性方程:
$$ho = q\left(N_D + p - n - N_A - n_D + p_A\right)$$

由电中性方程与质量作用定理
$$ightarrow n = rac{N_D}{2} igg[1 + \sqrt{1 + ig(4 n_i^2/N_D^2ig)} igg]$$

杂志饱和电离: $E_F=E_c+k_0T\ln(rac{N_D}{N_C})$ $E_F=E_{
m i}+k_0T\ln(rac{N_D}{n_i})$

简并半导体判断条件:

$$\left\{egin{aligned} E_c - E_F > 3k_0T, 非简并\ 0 < E_c - E_F < 3k_0T, 弱简并\ E_c - E_F < 0, 简并 \end{aligned}
ight.$$

简并半导体: $N_D=0.68N_c[1+2\exp(\frac{\triangle E_D}{k_0T})]$

电离杂质散射: $P_i \propto N_i T^{-\frac{3}{2}}$

长纵声学波: $P_s \propto T^{\frac{3}{2}}$

均匀导体的电流密度: $J=rac{I}{s}=rac{V}{Rs}=rac{l|E|}{Rs}=\sigma|E|$

平均迁移率: $\mu = \frac{q\tau}{m_{\pi}^*}$

 $\sigma = nq\mu_{
m n} + pq\mu_{
m p}$

迁移率: $\mu = \frac{q}{m^*} \frac{1}{AT^{\frac{3}{2}} + BN_i T^{-\frac{3}{2}}}$

对于n型半导体温度不太高时 $R_H \approx -\frac{1}{nq}$

霍尔效应: 对于p型半导体温度不太高时 $R_H \approx \frac{1}{pq}$

本征情况
$$R_H pprox rac{1-b^2}{n_i g(1+b)^2}$$

非子复合: U = R - G R = rnp $G = R_0 = rn_0p_0$

直接复合: $au = \frac{\Delta p}{U_d} = \frac{1}{r[(n_0+p_0)+\Delta p]}$

俘获和发射电子能力联系: $s_n = r_{\mathrm{n}} n_1$ $n_1 = N_c \exp(-\frac{E_c - E_t}{k_o T})$

通过复合中心复合:

 $U = rac{N_t r_n r_p (np - n_i^2)}{r_n (n+n_1) + r_p (p+p_1)} = rac{(np - n_i^2)}{ au_p (n+n_1) + au_n (p+p_1)} \quad au = rac{\Delta p}{U} = rac{r_n (n_0 + n_1 + \Delta p) + r_p (p_0 + p_1 + \Delta p)}{N_t r_n r_n (n_0 + p_0 + \Delta p)}$

 $ps:n_t = 可以通过 \frac{N_t(r_nn+r_pp_1)}{r_n(n+n_1)+r_n(p+p_1)}$ 推得另外书上和ppt中的公式是错的

肖克利-瑞德公式: $au=rac{\Delta p}{U}= au_prac{n_0+n_1}{n_0+p_0}+ au_nrac{p_0+p_1}{n_0+p_0}$ $au= au_p=rac{1}{N_tr_n}$ $au= au_n=rac{1}{N_tr_n}$

能级上电子积累: $\Delta n_t = rac{N_t n_1}{(n_0 + n_1)^2} \Delta n$ $(\Delta n_t)_{max} = rac{N_t}{4n_0} \Delta n$

一维扩散方程: $\frac{\partial \Delta p(x)}{\partial t} = D_p \frac{d^2 \Delta p(x)}{dx^2} - \frac{\Delta p(x)}{\tau}$ 一维稳态扩散方程: $-\frac{dS_p(x)}{dx} = D_p \frac{d^2 \Delta p(x)}{dx^2} = \frac{\Delta p(x)}{\tau}$

表明非平衡载流子浓度从光照表面向内部按指数衰减: $\Delta p(x) = (\Delta p)_0 e^{-x/L_p}$

爱因斯坦关系式: $\frac{D}{u} = \frac{kT}{a}$

连续性方程: $\frac{\partial p}{\partial t} = D_p \frac{\partial^2 p}{\partial x^2} - \mu_p |E| \frac{\partial p}{\partial x} - \mu_p p \frac{\partial |E|}{\partial x} + g_p - \frac{\Delta p}{\tau}$

线性缓变结: $N_D - N_A = \alpha_i(x - x_i)$

突变结接触电势差: $qV_D=E_{Fn}-E_{Fp}$ $V_D=rac{kT}{q}\ln(rac{N_AN_D}{n^2})$

P-N结载流子分布: $p_{(x)} = n_i e^{\frac{E_i(x) - E_F}{kT}} = p_{P0} e^{\frac{E_F - E_i(x_P)}{kT}} e^{\frac{E_i(x)^2 - E_F}{kT}} = p_{P0} e^{\frac{-qV(x)}{kT}} = p_{N0} e^{\frac{qV_D - qV(x)}{kT}}$ $n_{(x)} = n_i e^{\frac{E_F - E_i(x)}{kT}} = n_{N0} e^{\frac{E_i(x_N) - E_F}{kT}} e^{\frac{E_F - E_i(x)}{kT}} = n_{N0} e^{\frac{qV(x) - qV_D}{kT}} = n_{P0} e^{\frac{qV(x)}{kT}}$

 $\mathbf{P}^{+}\mathbf{N}\left(N_{A}\gg\ N_{D}
ight) \quad X_{D}=\sqrt{rac{2arepsilon_{r}arepsilon_{0}V_{D}}{qN_{D}}}\longrightarrow X_{D}pprox x_{n} \qquad \mathbf{N}^{+}\mathbf{P}$ 结 $\left(N_{D}\gg N_{A}
ight) \quad X_{D}=\sqrt{rac{2arepsilon_{r}arepsilon_{0}V_{D}}{qN_{A}}}\longrightarrow$

线性缓变结: $X_D = \left(\frac{12\varepsilon_r \varepsilon_0 V_D}{a\alpha}\right) 1/3$

正偏压P-N结: $\Delta n(x) = \Delta n(-x_p) \exp\left(rac{x+x_p}{L_n}
ight)$ $\Delta p(x) = \Delta p(x_n) \exp\left(-rac{x-x_n}{L_n}
ight)$

反偏压P-N结: $\Delta n(x) = -n_{p0} \exp\left(rac{x+x_p}{L_n}
ight)$ $\Delta p\left(x
ight) = -p_{n0} \exp\left(-rac{x-x_n}{L_p}
ight)$

理想P-N结I-V特性: $J=J_s\left|\exp\left(rac{qV}{kT}
ight)-1
ight|$ $J_s=\left(rac{qD_pn_i^2}{L_pN_D}+rac{qD_nn_i^2}{L_nN_A}
ight)$

理想P-N结I-V特性修正:

正向偏压: $\frac{J_{fd}}{J_c} \propto \frac{2n_i L_p}{N_D X_D} \exp(qV/2kT)$

反向偏压:

 $J_G = qGX_D = q\frac{n_i}{2\tau}X_D$

 $rac{J_{rd}}{J_G}=2rac{n_i}{N_D}rac{L_p}{X_D}$

平行板电容: $C_T = \frac{A\varepsilon_0\varepsilon_r}{X_D}$

泊松方程: $\frac{d^2V}{dx^2} = -\frac{\rho(x)}{\rho(x)}$

肖特基二极管空间电荷区宽: $d=\left[rac{2arepsilon_0arepsilon_r}{qN_D}(\phi_{ns}-\phi_n)
ight]^{1/2}=\left(rac{2arepsilon_0arepsilon_r}{qN_D}V_D
ight)^{1/2}$

适用于势垒宽度>>电子平均自由程:

 $J = J_{_{SD}}[\exp(qV/kT) - 1] \quad J_{_{SD}} = rac{q^2D_nn_0}{kT} [rac{2qN_D}{arepsilon_D}(V_D - V)]^{rac{1}{2}} \exp(rac{-qV_D}{kT})$

表面空间电荷层的电场:

 $E^2(x) = \left(rac{2kT}{q}
ight)^2 \left(rac{q^2p_{p0}}{2arepsilon_s kT}
ight) \left\{ \left[\exp\left(-rac{qV}{kT}
ight) + rac{qV}{kT} - 1
ight] + rac{n_{p0}}{p_{p0}} \left[\exp\left(rac{qV}{kT}
ight) - rac{qV}{kT} - 1
ight]
ight\}$

$$E(x)=\pmrac{2kT}{qL_D}F\left(rac{qV(x)}{kT},rac{n_{p0}}{p_{p0}}
ight) \quad L_D=\left(rac{2arepsilon_sKT}{q^2p_{p0}}
ight)^{1/2}$$

高斯原理: $Q_s = -\varepsilon_s E_s$

耗尽层宽度最大值: $d_{\max} = \left(\frac{2\varepsilon_s}{q} \frac{2V_B}{N_A}\right)^{1/2}$ 外加电场被反型层屏蔽,耗尽层宽度达到最大

$$C_s = \left|rac{dQ_s}{dV_s}
ight| = rac{arepsilon_s}{L_D} \Big\{ \left[-\exp\left(-rac{qV_s}{kT}
ight) + 1
ight] + rac{n_{p0}}{p_{p0}} \left[\exp\left(rac{qV_s}{kT}
ight) - 1
ight] \Big\} / F\left(rac{qV_s}{kT}, rac{n_{p0}}{p_{p0}}
ight)$$

绝缘层单位面积电容: $C_{ox} = \frac{\mathcal{E}_{ox}}{d_{ox}}$

平带电容:

$$C_{FBS} = \lim_{V_s o 0} rac{dQ_s}{dV_s} = rac{\sqrt{2}arepsilon_s}{L_D} \Biggl(1 + rac{n_{p0}}{p_{p0}}\Biggr)^{1/2} pprox rac{\sqrt{2}arepsilon_s}{L_D} \quad C_{_{FB}} = C_{_{ox}}/1 + rac{arepsilon_{ox}}{d_{ox}} \Biggl(rac{kT}{q^2N_A oldsymbol{arepsilon}_s}\Biggr)^{rac{1}{2}}$$

高频情况反型层电子产生复合更不上高频信号的变化: $\frac{C'_{\min}}{C_{\mathrm{ox}}} = \frac{1}{1+\frac{4\varepsilon_skT}{c_s}\ln\left(\frac{N_A}{n_i}\right)]^{1/2}}$

阈值电压:
$$V_T = \phi_{ms} - rac{Q_{ox}}{C_{ox}} - rac{Q_B}{C_{ox}} + 2\phi_F$$

$$V_n = -V_{ms} - rac{Q_{lpha x}}{C_{lpha x}} + rac{q N_d x_{d max}}{C_{lpha x}} + rac{2kT}{q} \ln rac{N_A}{n_i}$$

$$V_p = -V_{ms} - rac{Q_{lpha x}}{C_{lpha x}} - rac{q N_D x_{d ext{max}}}{C_{lpha x}} - rac{2kT}{q} ext{ln} rac{N_D}{n_i}$$

反型层电荷: $Q_n(y) = -C_{oX}[V_{GS} - V(y) - V_T]$

萨支唐方程: $I_{DS}=eta\left[(V_{GS}-V_T)V_{DS}-rac{1}{2}V_{DS}^2
ight]$ $eta\equivrac{\mu_nWC_{ox}}{L}$

沟道夹断: $I_{DSat} = \frac{\beta}{2}(V_{GS} - V_T)^2$ $V_{DSat} \equiv V_{GS} - V_T$